# PMEG1030EH; PMEG1030EJ

10 V, 3 A ultra low V<sub>F</sub> MEGA Schottky barrier rectifiers
Rev. 04 — 15 January 2010 Product d

Product data sheet

### **Product profile**

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection encapsulated in small SMD plastic packages.

Table 1. **Product overview** 

Type number	Package		Configuration
	NXP	JEITA	
PMEG1030EH	SOD123F	-	single isolated diodes
PMEG1030EJ	SOD323F	SC-90	single isolated diodes

### 1.2 Features

Forward current: 3 A Reverse voltage: 10 V

Ultra low forward voltage

Small and flat lead SMD package

## 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switched-mode power supply
- Inverse polarity protection
- Low power consumption applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F</sub>	forward current	$T_{sp} \leq 55  ^{\circ}C$	-	-	3	Α
$V_R$	reverse voltage		-	-	10	V
$V_{F}$	forward voltage	I <sub>F</sub> = 3 A	<u>[1]</u> _	390	530	mV

[1] Pulse test:  $t_0 \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



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# 2. Pinning information

Table 3. Pinning

10010 01	9	
Pin	Description	Simplified outline Symbol
1	cathode	[1]
2	anode	1 <del>1</del> 2 sym001
		001aab540

<sup>[1]</sup> The marking bar indicates the cathode.

# 3. Ordering information

Table 4. Ordering information

Type number	Package	Package			
	Name	Description	Version		
PMEG1030EH	-	plastic surface mounted package; 2 leads	SOD123F		
PMEG1030EJ	SC-90	plastic surface mounted package; 2 leads	SOD323F		

# 4. Marking

Table 5. Marking codes

Type number	Marking code
PMEG1030EH	AC
PMEG1030EJ	E7

## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{R}$	reverse voltage		-	10	V
I <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 55 °C	-	3	Α
I <sub>FRM</sub>	repetitive peak forward current	$t_p \leq 1 \text{ ms; } \delta \leq 0.25$	-	5.5	Α
I <sub>FSM</sub>	non-repetitive peak forward current	t = 8 ms; square wave	[1] _	9	Α
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PMEG1030EH		<u>[1]</u> _	375	mW
			[2] _	830	mW
	PMEG1030EJ		[1] -	360	mW
			[2] _	830	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air					
	PMEG1030EH		[1][2]	-	-	330	K/W
			[2][3]	-	-	150	K/W
	PMEG1030EJ		[1][2]	-	-	350	K/W
			[2][3]	-	-	150	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point						
	PMEG1030EH			-	-	60	K/W
	PMEG1030EJ			-	-	55	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[2]</sup> For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses  $P_R$  are a significant part of the total power losses. Nomograms for determining the reverse power losses  $P_R$  and  $I_{F(AV)}$  rating will be available on request.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

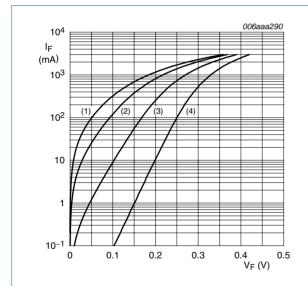
### 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \, ^{\circ}\text{C}$  unless otherwise specified.

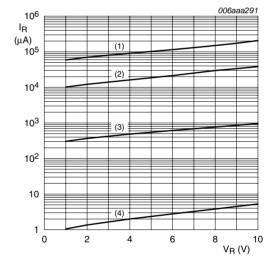
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage		<u>[1]</u>			
		I <sub>F</sub> = 0.01 A	-	100	130	mV
		I <sub>F</sub> = 0.1 A	-	170	200	mV
		I <sub>F</sub> = 1 A	-	280	350	mV
		I <sub>F</sub> = 3 A	-	390	530	mV
I <sub>R</sub>	reverse current	$V_R = 5 V$	-	0.55	2	mA
		V <sub>R</sub> = 8 V	-	0.8	2.5	mA
		V <sub>R</sub> = 10 V	-	1	3	mA
$C_d$	diode capacitance	$V_R = 1 V$ ; $f = 1 MHz$	-	70	85	pF

[1] Pulse test:  $t_0 \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



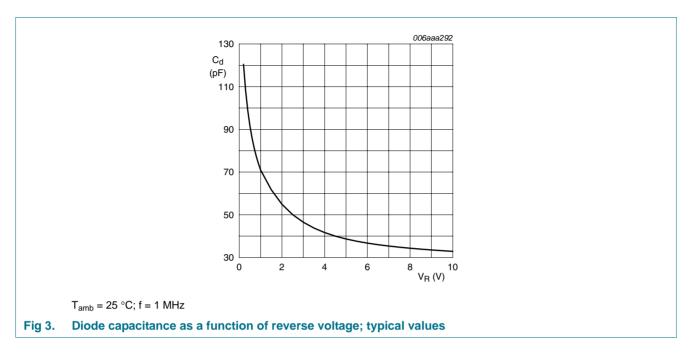
- (1)  $T_{amb} = 125 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values

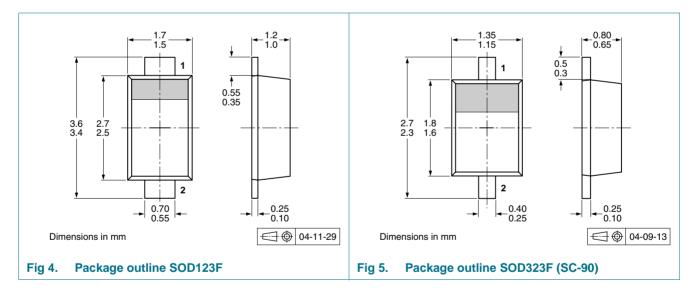


- (1)  $T_{amb} = 125 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values



# 8. Package outline



# 9. Packing information

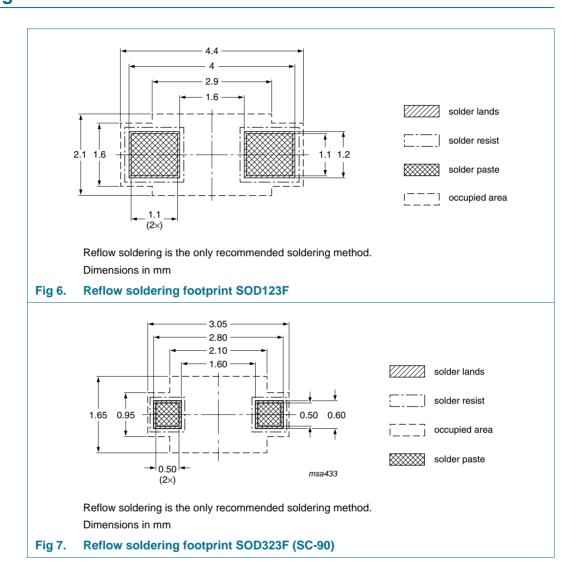
#### Table 9. Packing methods

The -xxx numbers are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMEG1030EH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135
PMEG1030EJ	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see Section 13.

## 10. Soldering



# 11. Revision history

### Table 10. Revision history

**Product data sheet** 

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG1030EH_EJ_4	20100115	Product data sheet	-	PMEG1030EH_EJ_3
Modifications:		eet was changed to reflect w legal definitions and disc		
PMEG1030EH_EJ_3	20050602	Product data sheet	-	PMEG1030EH_EJ_2
PMEG1030EH_EJ_2	20050405	Product data sheet	-	PMEG1030EJ_1
PMEG1030EJ_1	20050124	Product data sheet	-	-

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#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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